General Description

The WSK200N08A is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .
The WSK200N08A meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

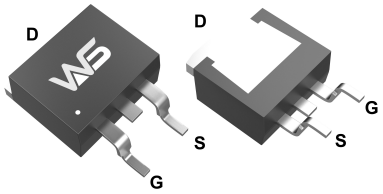
Product Summery

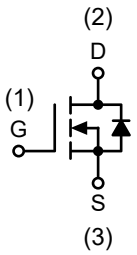
BV_{DSS}	R_{DSON}	I_D
80V	3mΩ	200A

Applications

- High power DC/DC converters and switch mode power supply
- DC Motor control and Class D Amplifier

TO-263-2L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	±25	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	200	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	144	A
I_{DM}	Pulsed Drain Current[2],T_C=25°C	790	A
EAS	Avalanche Energy, Single pulse,L=0.5mH	1496	mJ
I_{AS}	Avalanche Current, Single pulse,L=0.5mH	200	A
P_D@T_C=25℃	Total Power Dissipation[4]	345	W
P_D@T_C=100℃	Total Power Dissipation[4]	173	W
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.43	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	80	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.096	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V,I_D=100A	---	3.0	4.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.5	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±25V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.2	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=80V , V_{GS}=10V , I_D=30A	---	197	---	nC
Q_{gs}	Gate-Source Charge		---	31	---	
Q_{gd}	Gate-Drain Charge		---	75	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3Ω, I_D=30A	---	28	---	ns
T_r	Rise Time		---	18	---	
$T_{d(off)}$	Turn-Off Delay Time		---	42	---	
T_f	Fall Time		---	54	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	8154	---	pF
C_{oss}	Output Capacitance		---	1029	---	
C_{rss}	Reverse Transfer Capacitance		---	650	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.5mH , I_{AS}=28A	160	---	---	mJ

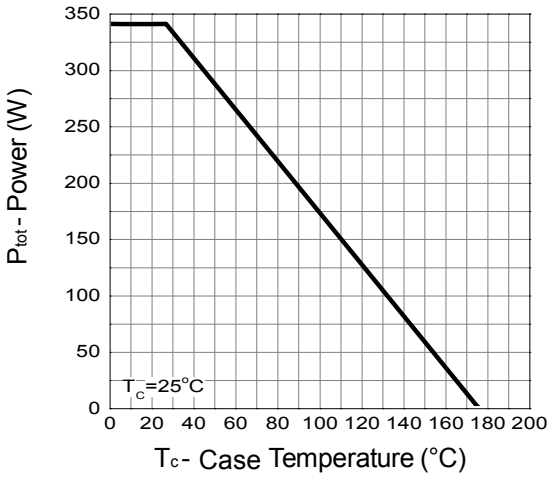
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	200	A
I_{SM}	Pulsed Source Current[2,6]		---	---	350	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=15A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=15A,dI/dt=100A/μs,T_J=25℃	---	30	---	nS
Q_{rr}	Reverse Recovery Charge		---	52	---	nC

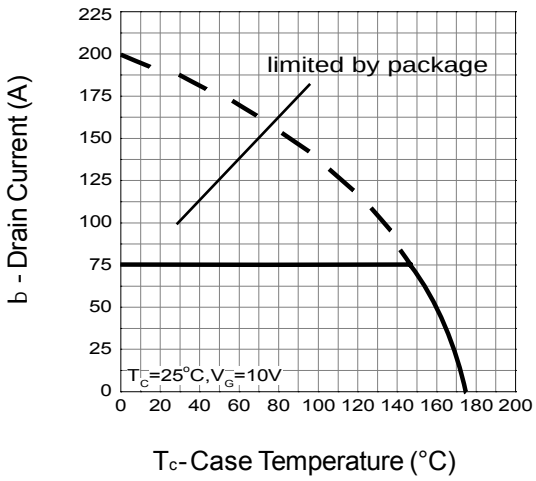
Note * : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Typical Operating Characteristics

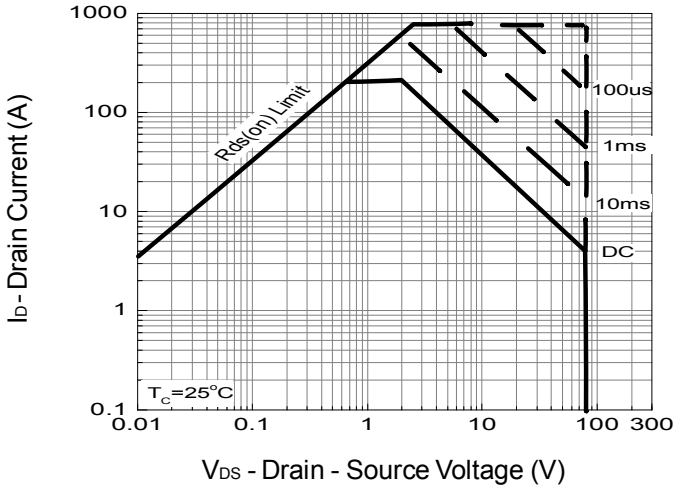
Power Dissipation



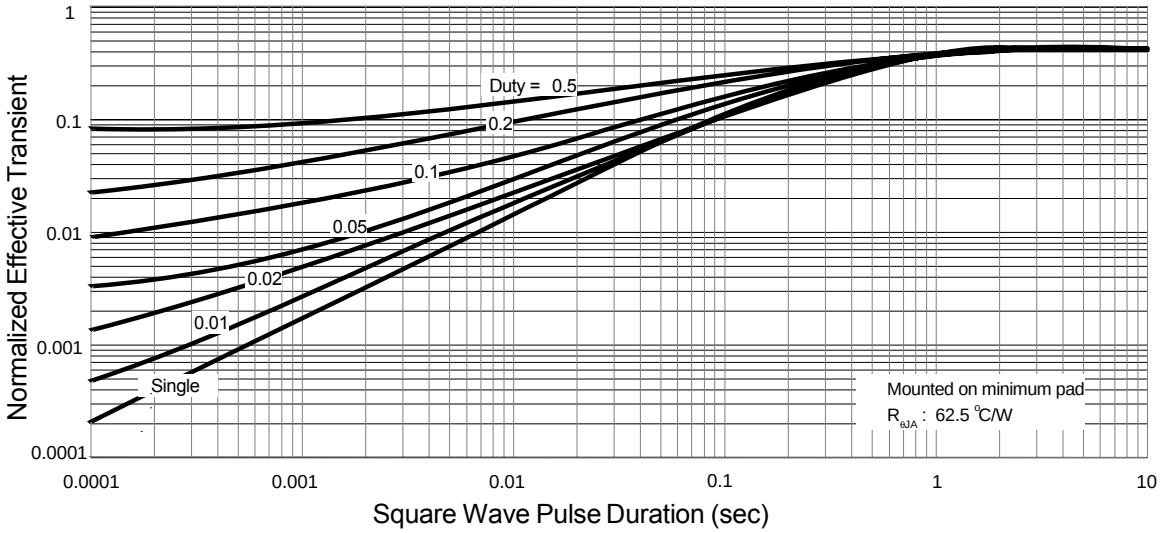
Drain Current



Safe Operation Area

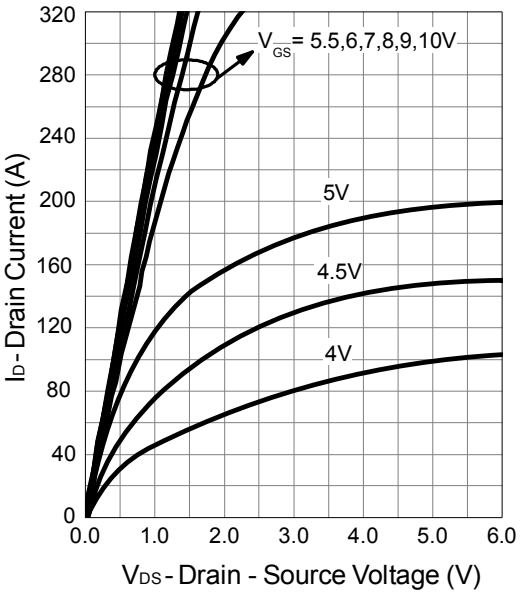


Thermal Transient Impedance

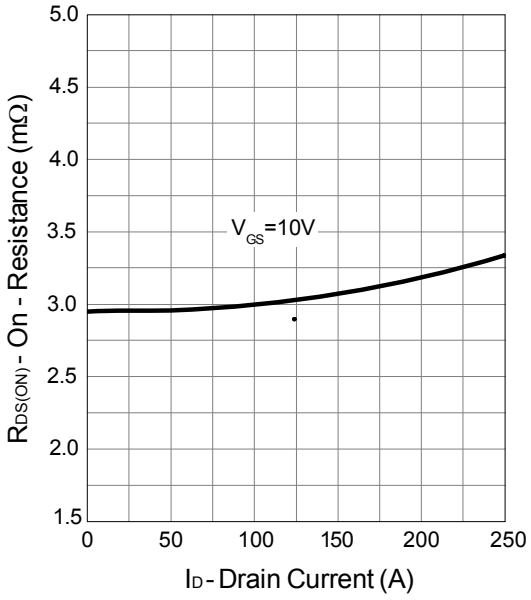


Typical Operating Characteristics (Cont.)

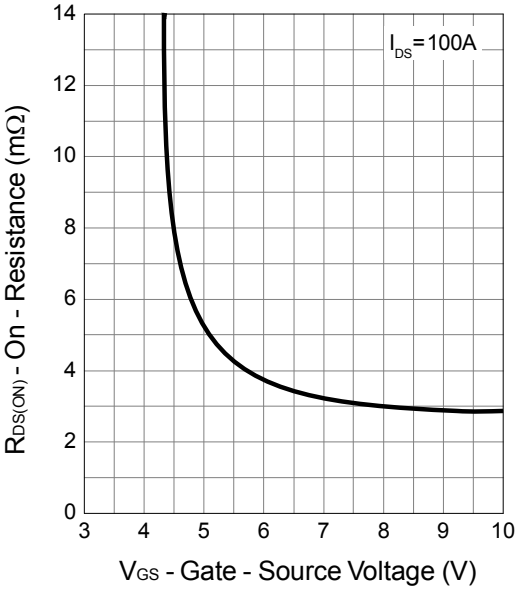
Output Characteristics



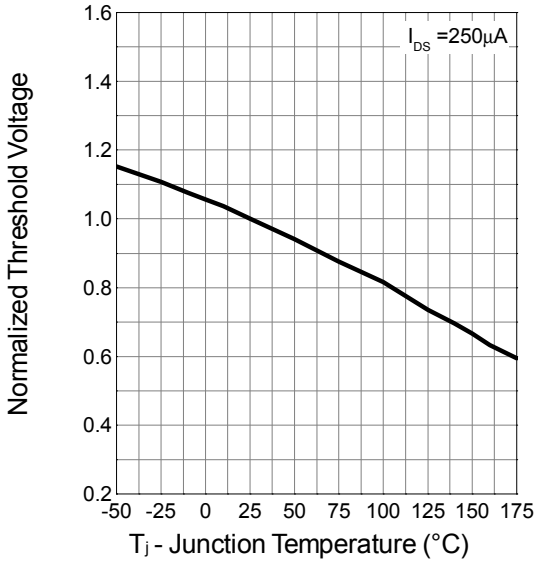
Drain-Source On Resistance



Gate-Source On Resistance

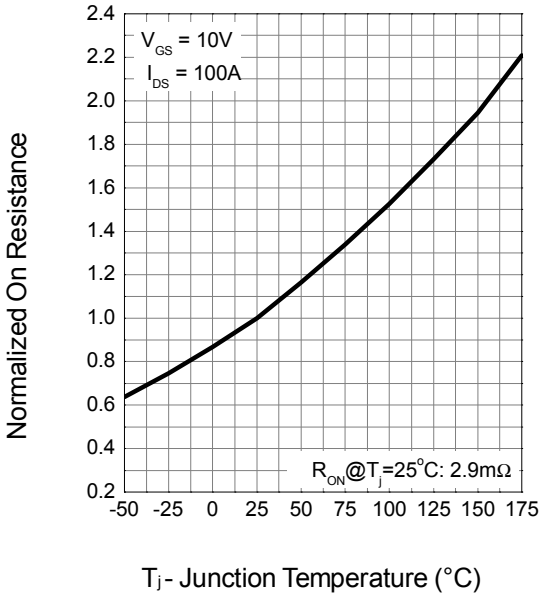


Gate Threshold Voltage

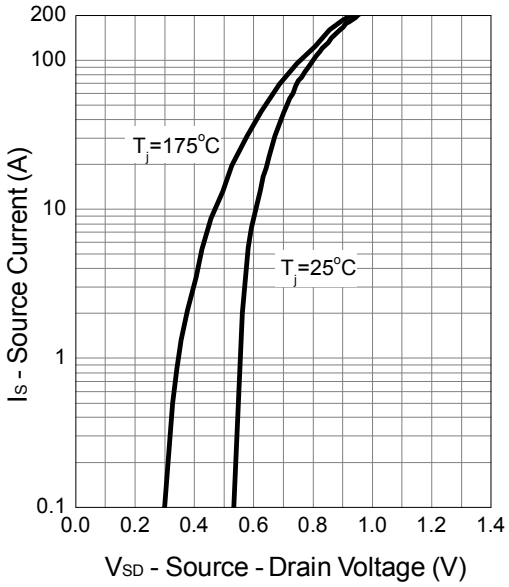


Typical Operating Characteristics (Cont.)

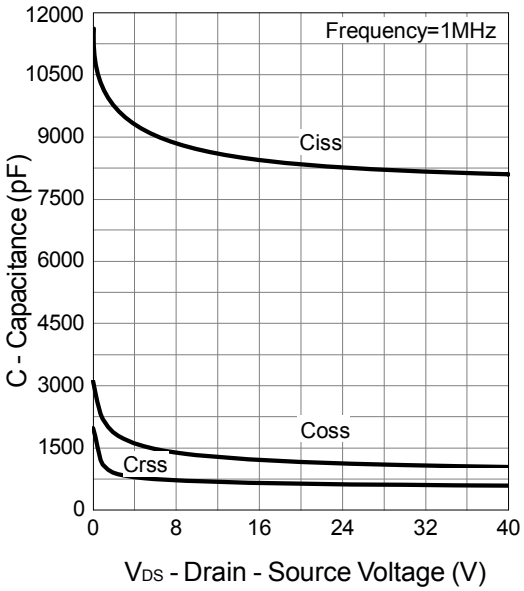
Drain-Source On Resistance



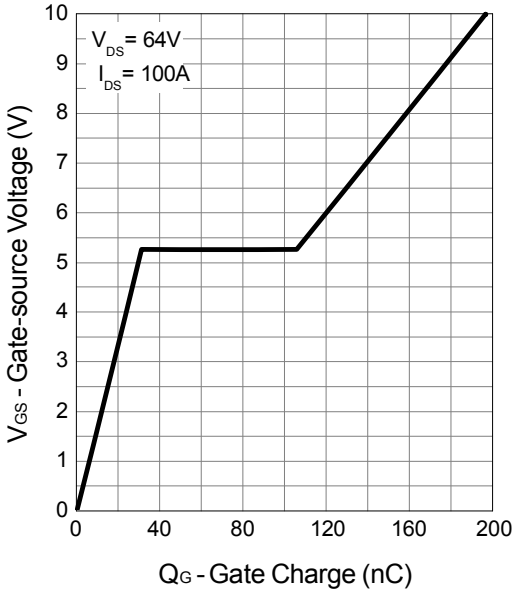
Source-Drain Diode Forward



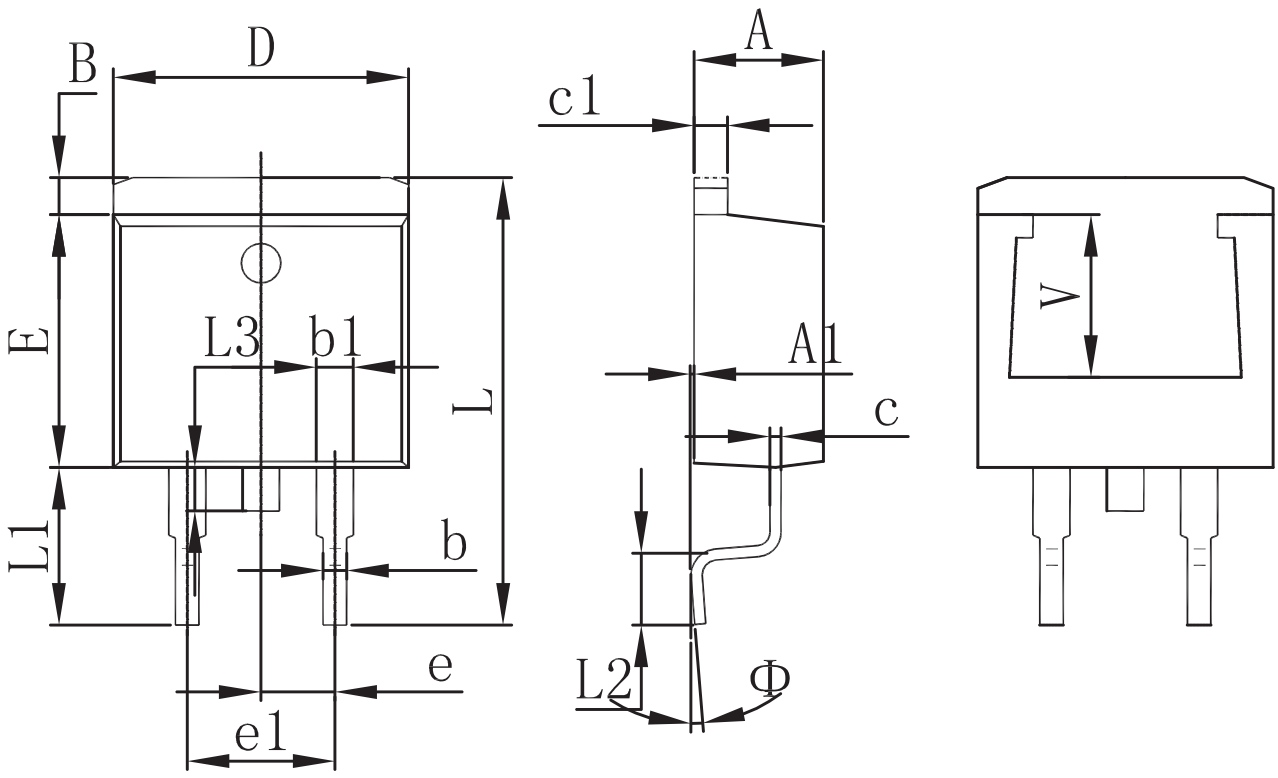
Capacitance



Gate Charge



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220REF.	

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